

**TRIACS  
SILICON BIDIRECTIONAL THYRISTORS**

**TRIACS  
1 AMPERES RMS  
800 VOLTS**

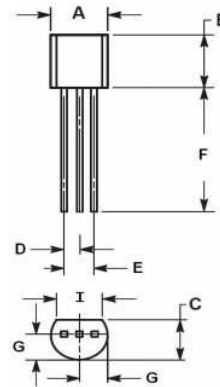
**FEATURES**

- Passivated die for reliability and uniformity
- Three-quadrant triggering Triac
- Over 800V  $V_{DRM}/V_{RRM}$
- Low level triggering and holding characteristics
- Logic control compatible
- False turn-on voltage up 600V by dv/dt
- Qualified to AEC-Q101 Rev\_C

**APPLICATIONS**

- General purpose motor control
- Small loads in washing machines
- Solenoid drivers
- Digital control drivers

**TO-92**



TO-92		
DIM.	MIN.	MAX.
A	4.45	4.70
B	4.32	5.33
C	3.18	4.19
D	1.15	1.39
E	2.42	2.66
F	12.7	-----
G	2.04	2.66
I	3.43	-----

All Dimensions in millimeter

PIN ASSIGNMENT	
1	Main Terminal 1
2	Gate
3	Main Terminal 2



**ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C, unless otherwise specified.)**

**Absolute Ratings**

PARAMETER	SYMBOL	VALUE	UNIT
Peak repetitive off-state voltage ( T <sub>j</sub> = -40 to 125°C, Full sine wave, 50 to 60 Hz; Gate open) (Note 1)	$V_{DRM}$ $V_{RRM}$	800	V
On-stage RMS current (Full sine wave, T <sub>c</sub> = 110°C )	$I_{T(RMS)}$	1	A
Peak non-repetitive surge current ( one full cycle 60 Hz, T <sub>j</sub> = 25°C)	$I_{TSM}$	13.7	A
Circuit fusing consideration ( t = 8.3ms)	$I^2T$	0.4	A <sup>2</sup> S
Peak gate current	$I_{GM}$	2	A
Peak gate power	$P_{GM}$	5	W
Average gate power	$P_{G(AV)}$	0.1	W
Operating junction temperature range	T <sub>j</sub>	-40 to +125	°C
Storage temperature range	T <sub>STG</sub>	-40 to +150	°C

**Note :**

- (1)  $V_{DRM}$  and  $V_{RRM}$  for all types can be applied on a continuous basis.  
Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

REV. 0, JUL-2016, KTXD27

# T1M10T800A

CHARACTERISTIC & CURVES ( $T_j = 25^\circ\text{C}$ , unless otherwise specified.)



## Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal resistance from junction	Rth(j-c)	60	$^\circ\text{C/W}$
	Rth(j-a)	150	
Maximum lead temperature for soldering purposes (1/8" form case for 10 seconds)	$T_L$	260	$^\circ\text{C}$

## Static Characteristics

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Threshold Voltage <sup>(1)</sup> @ $T_j = 125^\circ\text{C}$	$V_{to}$	--	--	0.9	V	
Dynamic resistors <sup>(1)</sup> @ $T_j = 125^\circ\text{C}$	$R_d$	--	--	390	m $\Omega$	
Peak repetitive forward or reverse blocking current ( $V_{AK} = \text{rated } V_{DRM}$ and $V_{RRM}$ , gate open)	$T_j = 25^\circ\text{C}$	$I_{DRM}$	--	--	5	$\mu\text{A}$
	$T_j = 125^\circ\text{C}$	$I_{RRM}$	--	--	0.5	mA

1. For both polarities of A2 referenced to A1.

## ON Characteristics

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Peak forward on-state voltage ( $I_{TM} = 1 \text{ A}$ @ $T_j = 25^\circ\text{C}$ )	$V_{TM}$	--	1.2	1.5	V
$V_D = V_{DRM}$ , $R_L = 100\Omega$ , $T_j = 125^\circ\text{C}$	$V_{GD}$	0.3	--	--	V
Gate trigger current ( $V_{AK} = 12\text{V}$ , $R_L = 100\Omega$ )	$I_{GT1}$ $I_{GT2}$ $I_{GT3}$	--	--	10	mA
Gate trigger voltage ( $V_{AK} = 12\text{V}$ , $R_L = 100\Omega$ )	$V_{GT1}$ $V_{GT2}$ $V_{GT3}$	--	--	1	V
Holding current ( $V_{AK} = 12\text{V}$ , $R_L = 100\Omega$ )	$I_{H1}$ $I_{H3}$	--	--	12	mA
Latching current ( $V_{AK} = 12\text{V}$ , $R_L = 100\Omega$ )	$I_{L1}$	--	--	12	mA
	$I_{L2}$	--	--	25	
	$I_{L3}$	--	--	12	

# T1M10T800A

CHARACTERISTIC & CURVES (T<sub>j</sub> = 25°C, unless otherwise specified.)



## Dynamic Characteristics

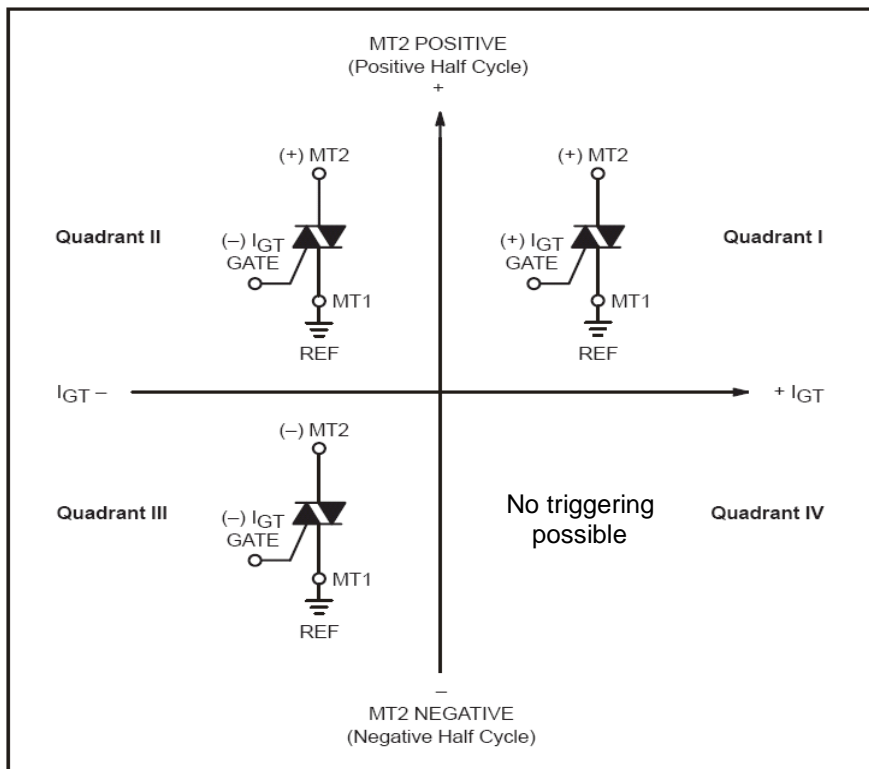
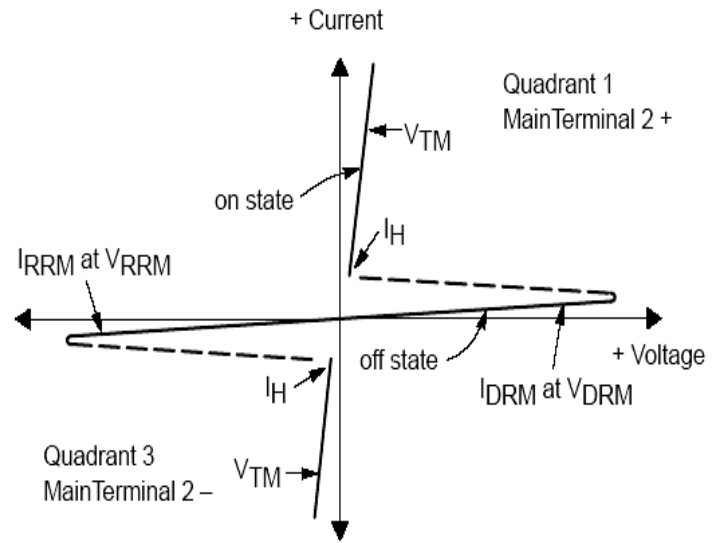
PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT
Critical rate of rise of off-stage voltage (V <sub>AK</sub> = 67% rated V <sub>DRM</sub> , @ T <sub>j</sub> = 125°C, gate open)		dv/dt	600	--	--	V/us
Rate of rise of on-state current (V <sub>DRM</sub> =maximum V <sub>DRM</sub> , T <sub>j</sub> = 125°C)		di/dt	--	--	100	A/us
Rate of change of commutating current	VD=400V, dv/dt(c)=10V/us, T <sub>j</sub> =125°C	di/dt(c)	4	--	--	A/ms
	Without snubber, VD=400V, T <sub>j</sub> =125°C		3	--	--	

# T1M10T800A

CHARACTERISTIC & CURVES ( $T_j = 25^\circ\text{C}$ , unless otherwise specified.)



Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
$I_H$	Holding Current



All polarities are referenced to MT1  
 With in-phase signal (using standard AC lines) quadrants I and III are used

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CHARACTERISTIC & CURVES ( $T_j = 25^\circ\text{C}$ , unless otherwise specified.)



Fig.1- Holding Current Variation

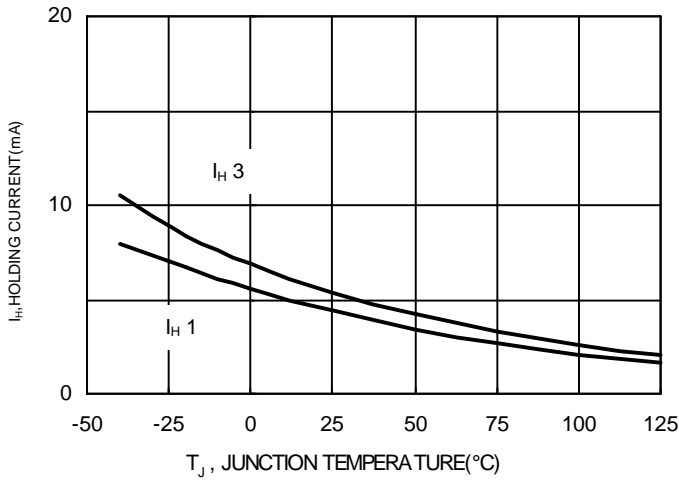


Fig.2- Gate Trigger Current Variation

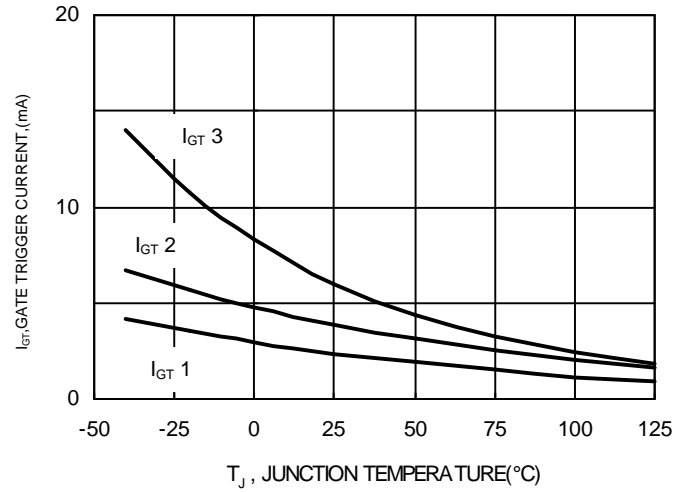


Fig.3- Gate Trigger Voltage Variation

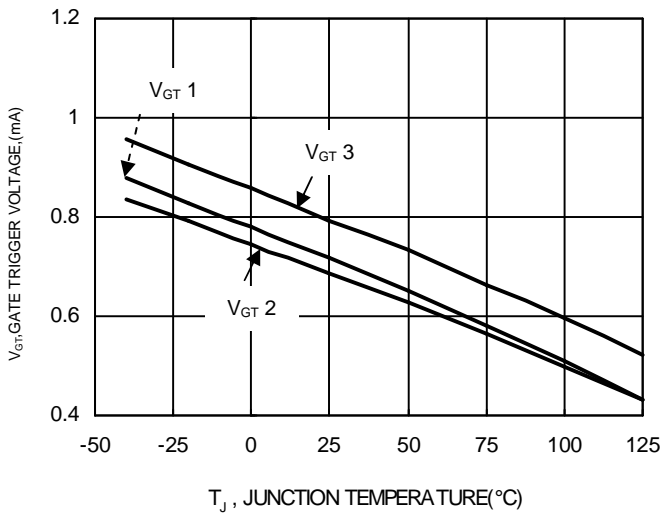


Fig.4- Typical Latching Current Versus Junction Temperature

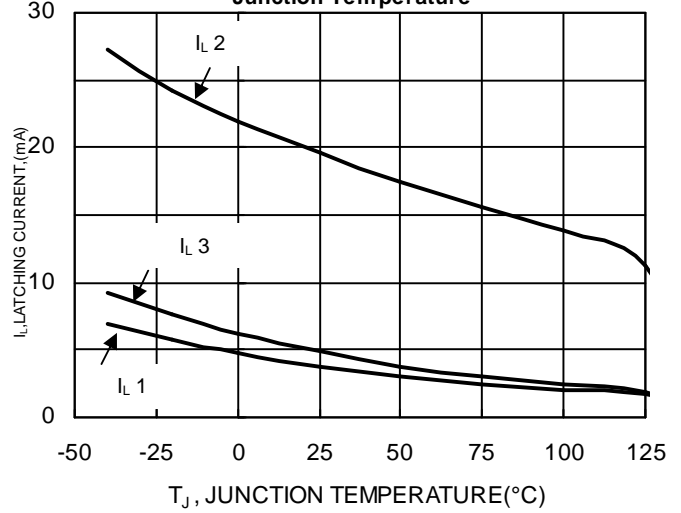


Fig.5- On-State Characteristics

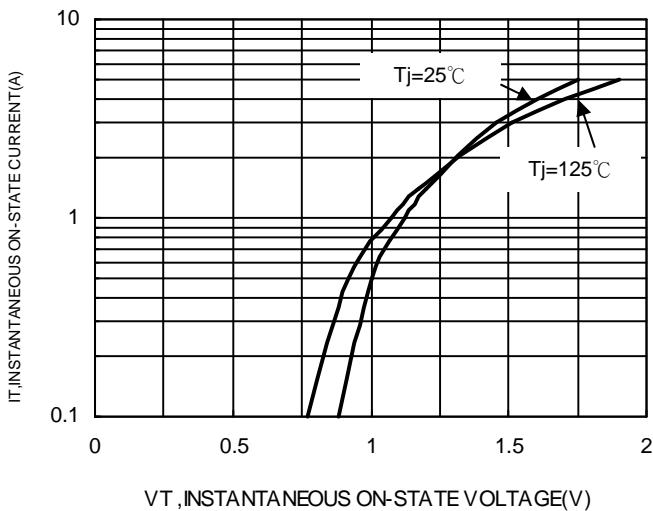
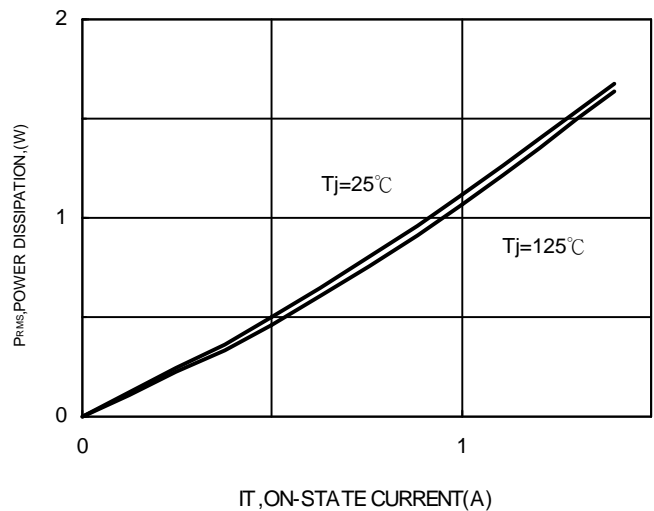


Fig.6- Power Dissipation versus  $I_T$



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